CIR-W4SUSW2616G

DDR4 WIDE TEMP. SO-DIMM 2666MHz 16GB

Description

This specification defines the electrical and mechanical requirements for 260 pin, 1.2 V (VDD), Double Data Rate, Synchronous DRAM Dual In-Line Memory Modules (DDR4 SDRAM SO-DIMM). This DDR4 SO-DIMM is intended for use as main memory when installed in PCs, laptops and other systems.

Reference design examples are included which provide an initial basis for DDR4 SO-DIMM designs.

Modifications to these reference designs may be required to meet all system timing, signal integrity and thermal requirements for DDR4-2666 support. All DDR4 SO-DIMM implementations must use simulations and lab verification to ensure proper timing requirement and signal integrity in the design.

Specifications

Density	16GB
Pin Count	260pin
Type	Unbuffered
Dimensions	69.60mm x 30.00mm
ECC	Non-ECC
Component Config	1G x 8 bit
Data Rate	2666 MHz
CAS Latency	19
Voltage	1.2V
PCB Layers	10
Operating Temp.(TCASE)	-40°C~+85°C
Module Ranks	Dual Rank

Features

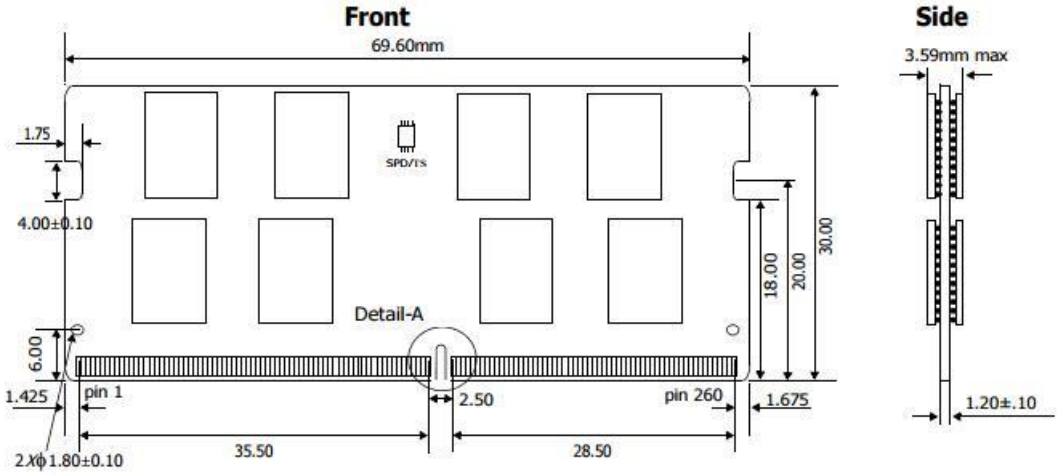
- JEDEC Standard 260-pin Dual In-Line Memory Module
- Intend for PC4-2666 applications
- Inputs and Outputs are SSTL-12 compatible
- VDD=VDDQ = 1.2V±0.06V (1.14V~1.26V)
- Programmable CAS Latency(posted CAS): 11,12,13,14,15,16,17,18,19
- Low-Power auto self-refresh (LPASR)
- SDRAMs have 16 internal banks for concurrent operation (4 Bank Group of 4 banks each)
- Normal and Dynamic On-Die Termination for data, strobe and mask signals
- Data bus inversion (DBI) for data bus
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the MRS
- Selectable BC4 or BL8 on-the fly (OTF)
- Fly-By topology
- Terminated control, command and address bus
- RoHS and Halogen free

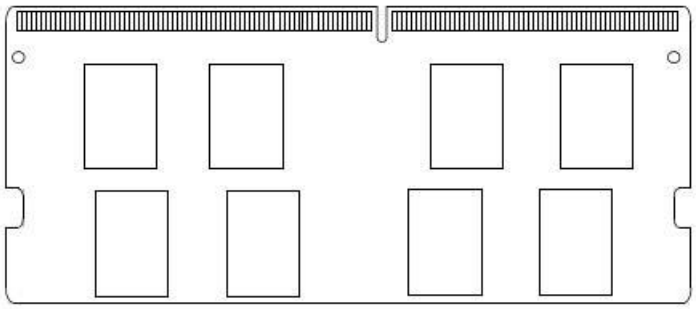
Speed Grade

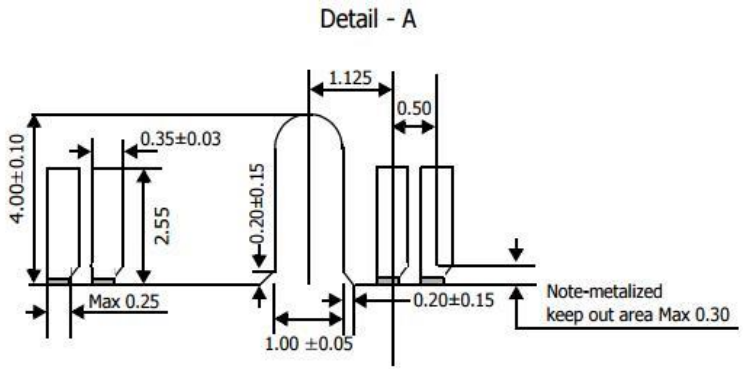
Frequency Grade	Data Transfer Rate	CAS Latency Support								CL-tRCD-tRP
		CL11	CL12	CL13	CL14	CL15	CL16	CL17	CL19	
DDR4-2666	PC4-21300	1600	1600	1866	1866	2133	2133	2400	2666	19-19-19

Package Dimensions

Unit: mm







Tolerances : ± 0.15mm unless otherwise specified